

to at least one said major surface thereof before said heating step with said wafer being in immediate heat transfer relation with the support during at least a portion of the coating application.

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Amend
Sub
C1

Please replace claim 3 with the following:

3. (amended) A method as set forth in claim 2 wherein said wafer is heated to a temperature of at least about 1250°C after said coating is applied and the cooling rate of the wafer is at least about 20°C/sec.

Please cancel claims 18-20.